



PJD70P03E-AU

30V N-Channel Enhancement Mode MOSFET

Voltage -30 V Current -52 A

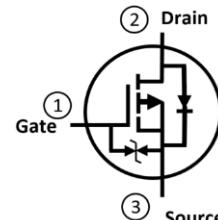
Features

- $R_{DS(ON)}$, $V_{GS} @ -10V$, $I_D @ -20A < 8.4m\Omega$
- $R_{DS(ON)}$, $V_{GS} @ -4.5V$, $I_D @ -10A < 13.5m\Omega$
- Excellent FOM
- Standard Level Drive
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : TO-252AA Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.297 grams

TO-252AA



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 25	
Continuous Drain Current (Note 3)	I_D	-52	A
		-36	
Pulsed Drain Current (Note 1)	I_{DM}	-208	W
Power Dissipation	P_D	79	
		39	
Continuous Drain Current (Note 4)	I_D	-13.4	A
		-11.2	
Power Dissipation	P_D	2.4	W
		1.7	
Single Pulse Avalanche Energy (Note 5)	E_{AS}	100	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~175	°C
Typical Thermal Resistance (Note 4)	Junction to Case	$R_{\theta JC}$	1.9 $^{\circ}\text{C}/\text{W}$
	Junction to Ambient	$R_{\theta JA}$	62.5



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Electrical Characteristics ($T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-1.7	-2.5	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-20A$	-	6.7	8.4	$m\Omega$
		$V_{GS}=-4.5V, I_D=-10A$	-	10.4	13.5	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0V$	-	-	-1	μA
Gate-Source Leakage Current	I_{GS}	$V_{GS}=\pm 25V, V_{DS}=0V$	-	-	± 10	μA
		$V_{GS}=\pm 10V, V_{DS}=0V$			± 1	
Dynamic (Note 6)						
Total Gate Charge	Q_g	$V_{DS}=-24V, I_D=-20A,$ $V_{GS}=-10V$	-	54	-	nC
Gate-Source Charge	Q_{gs}		-	6	-	
Gate-Drain Charge	Q_{gd}		-	17	-	
Input Capacitance	C_{iss}	$V_{DS}=-25V, V_{GS}=0V,$ $f=1MHz$	-	2310	-	pF
Output Capacitance	C_{oss}		-	332	-	
Reverse Transfer Capacitance	C_{rss}		-	256	-	
Gate resistance	R_g	$f=1MHz$	-	2.3	-	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=-24V, I_D=-20A,$ $V_{GS}=-10V, R_G=3\Omega$ (Note 2)	-	9	-	ns
Turn-On Rise Time	t_r		-	91	-	
Turn-Off Delay Time	$t_{d(off)}$		-	47	-	
Turn-Off Fall Time	t_f		-	99	-	
Drain-Source Diode						
Diode Forward Current	I_s	$T_c=25^\circ C$	-	-	-52	A
Pulsed Diode Forward Current	I_{SM}		-	-	-208	
Diode Forward Voltage	V_{SD}	$I_s=-20A, V_{GS}=0V$	-	-0.85	-1.3	V
Reverse Recovery Time	T_{rr}	$V_{GS}=0V, I_s=-20A$ $dI_s/dt=100A/\mu s$	-	22	-	ns
Reverse Recovery Charge	Q_{rr}		-	10	-	

NOTES :

1. Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.
2. Essentially independent of operating temperature typical characteristics.
3. The maximum current rating is package limited.
4. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
5. The test condition is $L=0.5mH, I_{AS}=-20A, V_{DD}=-30V, V_{GS}=-10V$, Starting $T_J=25^\circ C$.
6. Guaranteed by design, not subject to production testing.



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TYPICAL CHARACTERISTIC CURVES

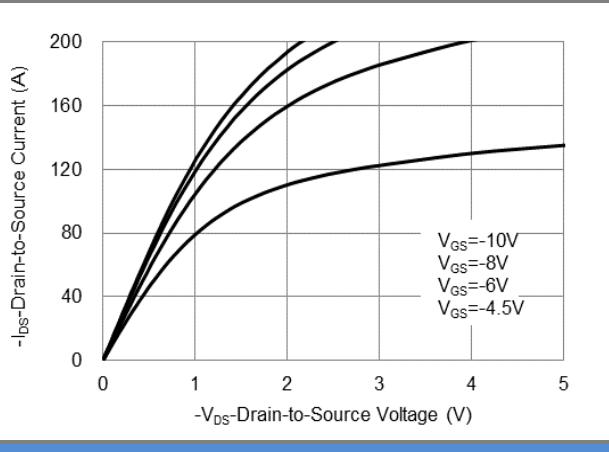


Fig.1 On-Region Characteristics

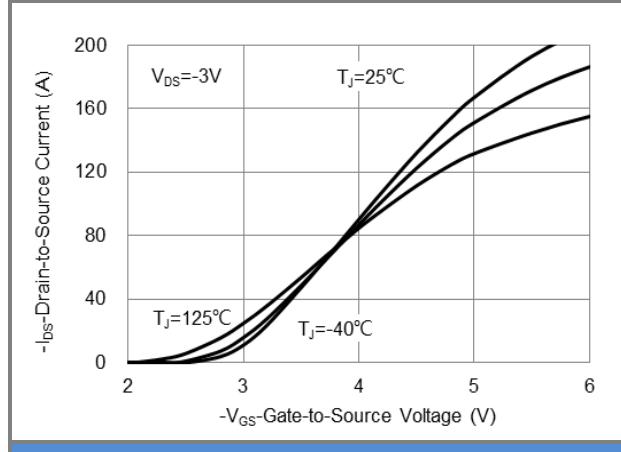


Fig.2 Transfer Characteristics

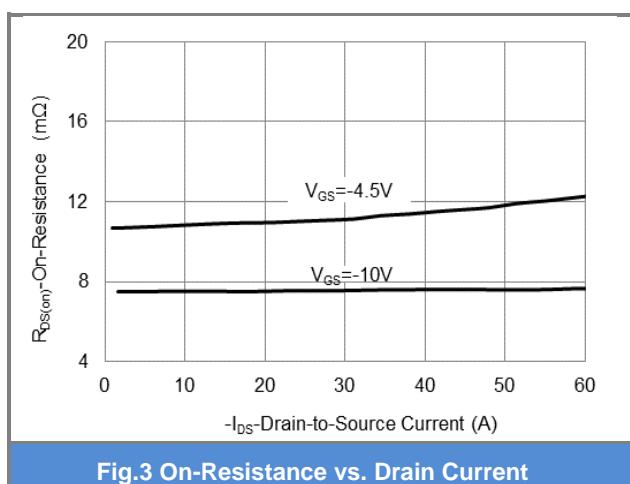


Fig.3 On-Resistance vs. Drain Current

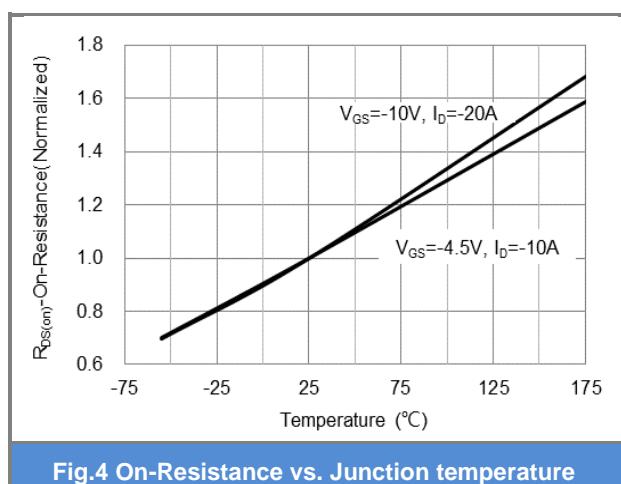


Fig.4 On-Resistance vs. Junction temperature

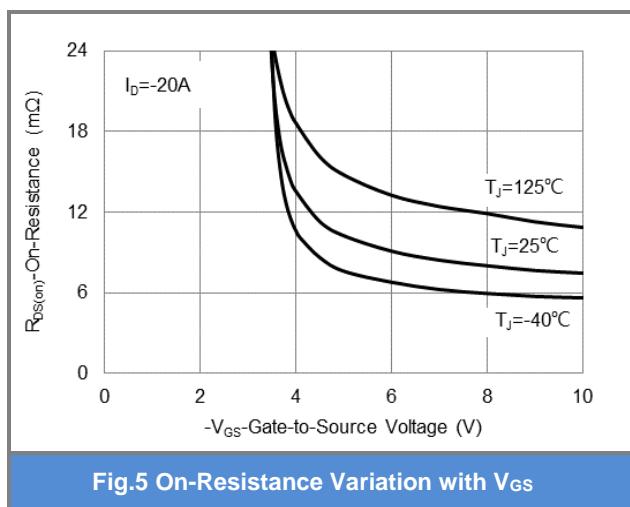


Fig.5 On-Resistance Variation with V_{GS}

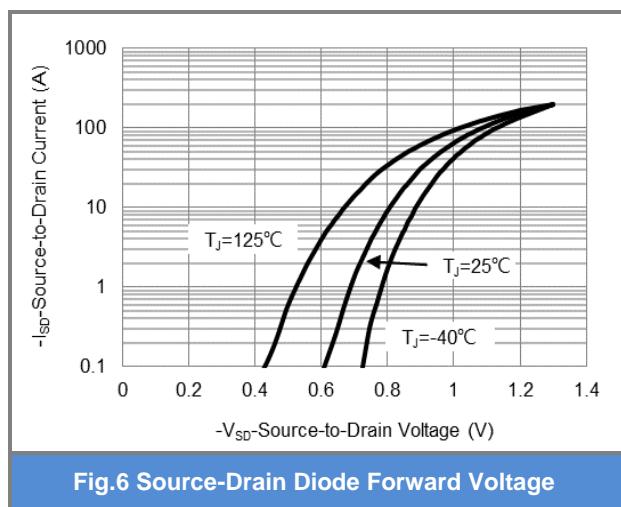


Fig.6 Source-Drain Diode Forward Voltage



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TYPICAL CHARACTERISTIC CURVES

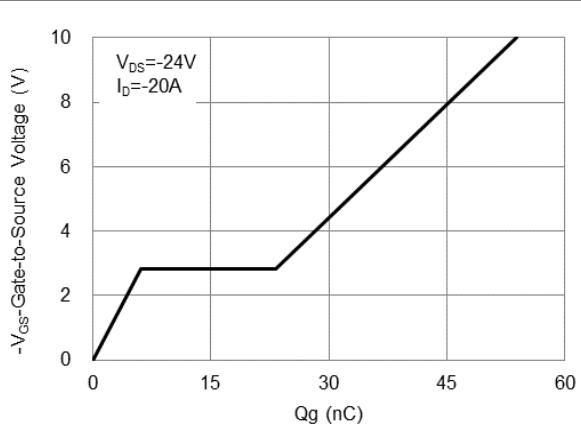


Fig.7 Gate-Charge Characteristics

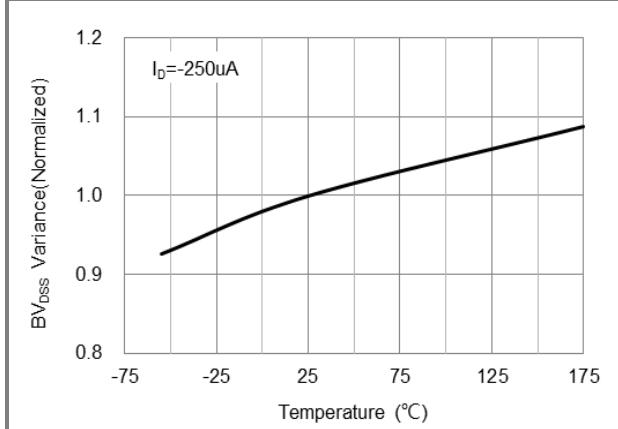


Fig.8 Breakdown Voltage Variation vs. Temperature

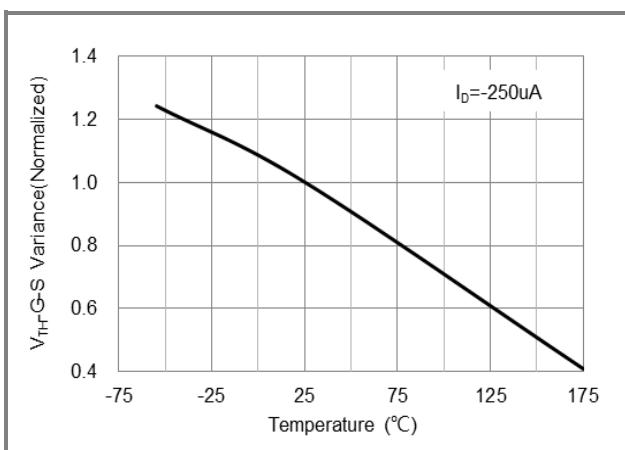


Fig.9 Threshold Voltage Variation with Temperature

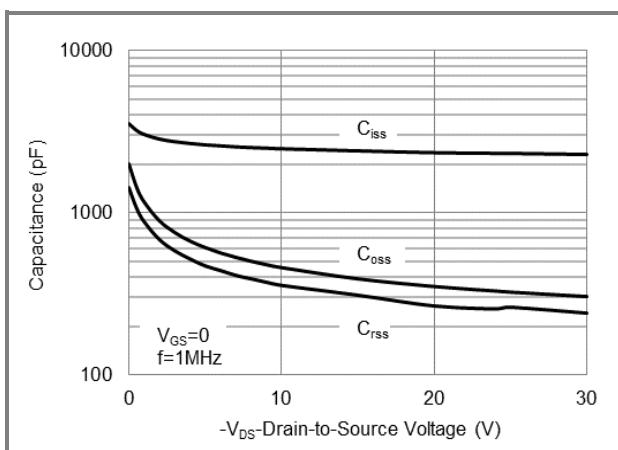


Fig.10 Capacitance vs. Drain-Source Voltage

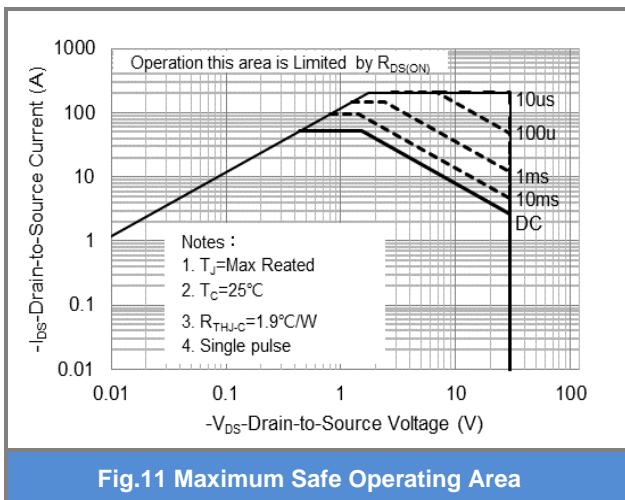


Fig.11 Maximum Safe Operating Area

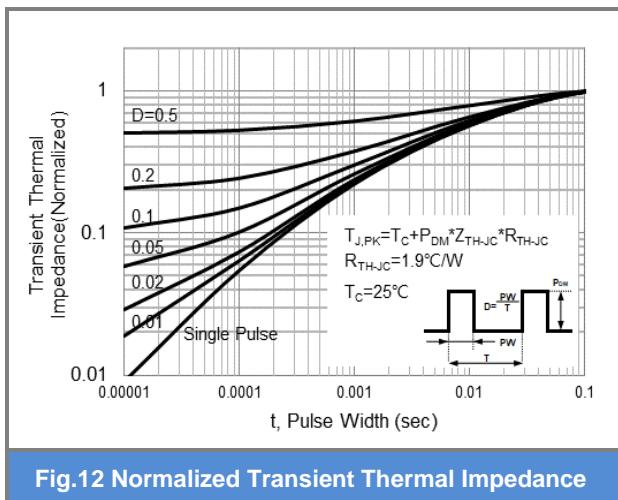


Fig.12 Normalized Transient Thermal Impedance

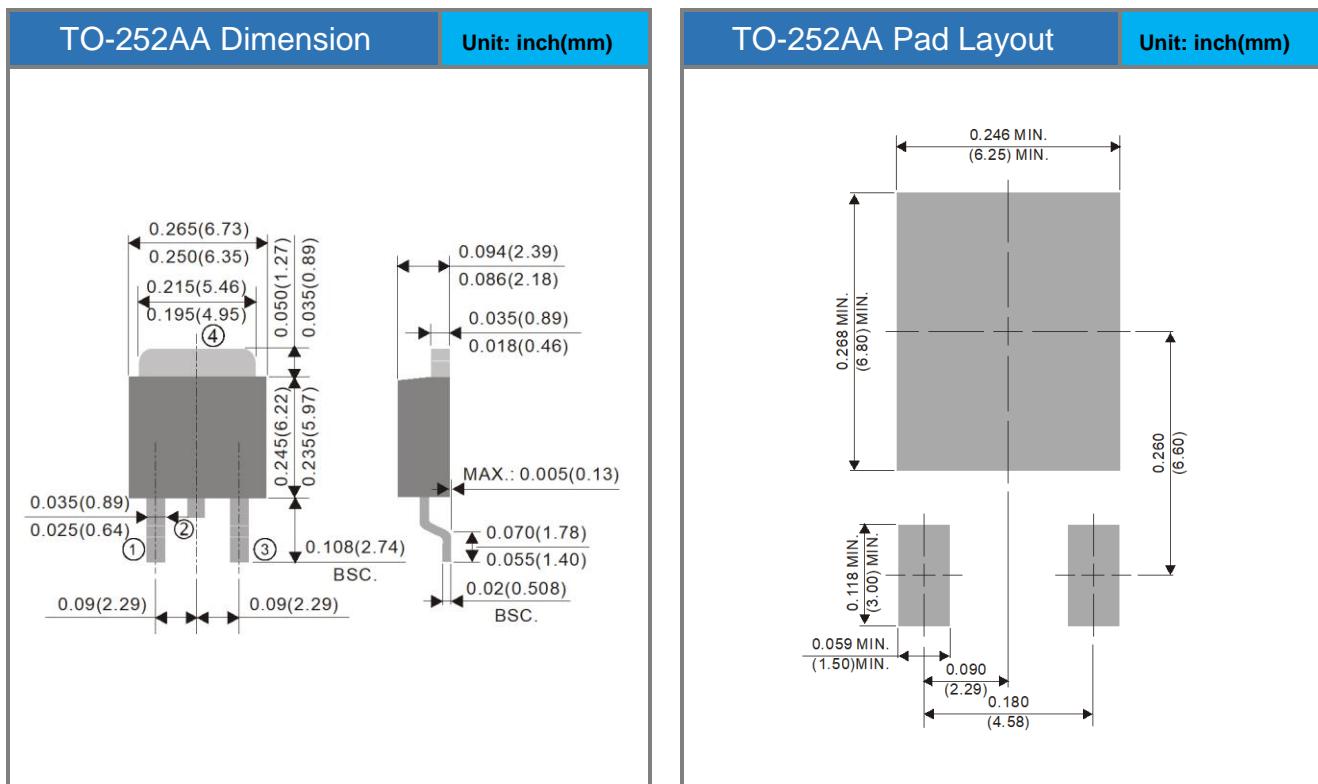


PJD70P03E-AU

Part No Packing Code Version

Part No Packing Code	Package Type	Packing type	Marking	Version
PJD70P03E-AU_R2_002A1	TO-252AA	3,000 pcs / 13" reel	D70P03E	Halogen free RoHS compliant

Packaging Information & Mounting Pad Layout



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